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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD

December 2014

FGL12040WD

1200 V, 40 A Field Stop Trench IGBT

Features

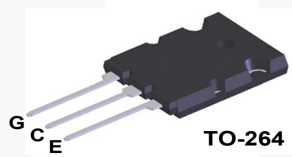
- Maximum Junction Temperature : $T_J = 150^oC$
- Positive Temperature Co-efficient for Easy Parallel Operating
- Low Saturation Voltage: $V_{CE(sat)}$ =2.3 V @ I_C = 40 A
- 100% of The Parts Tested for I_{LM}(1)
- Short Circuit Ruggedness > 5 us @ 150^{o}C
- High Input Impedance
- RoHS Compliant

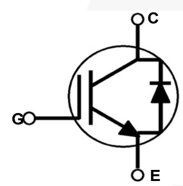
General Description

Using novel field stop IGBT technology, Fairchild's new series of field stop 2nd generation IGBTs offer the optimum performance for welder applications where low conduction and switching losses are essential.

Applications

- Only for Welder





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		FGL12040WD	Unit
V_{CES}	Collector to Emitter Voltage		1200	V
V_{GES}	Gate to Emitter Voltage		±25	V
	Transient Gate to Emitter Voltage		±30	V
I_C	Collector Current	@ T_C = 25^{o}C	80	A
	Collector Current	@ T_C = 100^{o}C	40	A
I_{LM} (1)	Clamped Inductive Load Current	@ T_C = 25^{o}C	100	A
I_{CM} (2)	Pulsed Collector Current		100	A
I_F	Diode Continuous Forward Current	@ T_C = 25^{o}C	80	A
	Diode Continuous Forward Current	@ T_C = 100^{o}C	40	A
I_{FM}(2)	Diode Maximum Forward Current		100	A
SCWT (3)	Short Circuit Withstand Time	@ T_C = 150^{o}C	5	us
P_D	Maximum Power Dissipation	@ T_C = 25^{o}C	391	W
	Maximum Power Dissipation	@ T_C = 100^{o}C	156	W
T_J	Operating Junction Temperature		-55 to +150	^{o}C
T_{stg}	Storage Temperature Range		-55 to +150	^{o}C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	^{o}C

Notes:
1. Vcc = 600 V, V_{GE} = 15 V, I_C = 100 A, R_G = 23 Ω , Inductive Load
2. Repetitive rating : Pulse width limited by max, junction temperature
3. V_{CC} = 600 V, V_{GE} = 12 V

Thermal Characteristics

Symbol	Parameter	FGL12040WD	Unit
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case	0.32	$^oC/W$
$R_{\theta JC}$(Diode)	Thermal Resistance, Junction to Case	1.0	$^oC/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	25	$^oC/W$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGL12040WD	FGL12040WD	TO-264	Tube	-	-	25

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0 V, I_C = 250 uA	1200	-	-	V
ΔBV_{CES} / ΔT_J	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0 V, I_C = 250 uA	-	1.2	-	V/^oC
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, V_{GE} = 0 V	-	-	250	uA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, V_{CE} = 0 V	-	-	±400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 40 mA, $V_{CE} = V_{GE}$	4.8	6.4	8.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 40 A, V_{GE} = 15 V T_C = 25^oC	-	2.3	2.9	V
		I_C = 40 A, V_{GE} = 15 V, T_C = 150^oC	-	2.5	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1MHz	-	2800	-	pF
C_{oes}	Output Capacitance		-	105	-	pF
C_{res}	Reverse Transfer Capacitance		-	60	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 40 A, R_G = 23 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25^oC	-	45	-	ns
t_r	Rise Time		-	70	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	560	-	ns
t_f	Fall Time		-	15	-	ns
E_{on}	Turn-On Switching Loss		-	4.1	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.0	-	mJ
E_{ts}	Total Switching Loss		-	5.1	-	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 40 A, R_G = 23 Ω, V_{GE} = 15 V, Inductive Load, T_C = 150^oC	-	40	-	ns
t_r	Rise Time		-	65	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	472	-	ns
t_f	Fall Time		-	51	-	ns
E_{on}	Turn-On Switching Loss		-	6.1	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.7	-	mJ
E_{ts}	Total Switching Loss		-	7.8	-	mJ

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V	-	226	-	nC
Q_{ge}	Gate to Emitter Charge		-	18	-	nC
Q_{gc}	Gate to Collector Charge		-	155	-	nC

Electrical Characteristics of the DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FM}	Diode Forward Voltage	I_F = 40 A, T_C = 25^{o}C	-	3.6	4.7	V
		I_F = 40 A, T_C = 150^{o}C	-	3.0	-	V
t_{rr}	Diode Reverse Recovery Time	V_R = 600 V, I_F = 40 A, di_F/dt = 200 A/us, T_C = 25^{o}C	-	71	-	ns
I_{rr}	Diode Peak Reverse Recovery Current		-	6.8	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	242	-	nC
E_{rec}	Reverse Recovery Energy	V_R = 600 V, I_F = 40A, di_F/dt = 200 A/us, T_C = 150^{o}C	-	440	-	uJ
t_{rr}	Diode Reverse Recovery Time		-	339	-	ns
I_{rr}	Diode Peak Reverse Recovery Current		-	14	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	2373	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

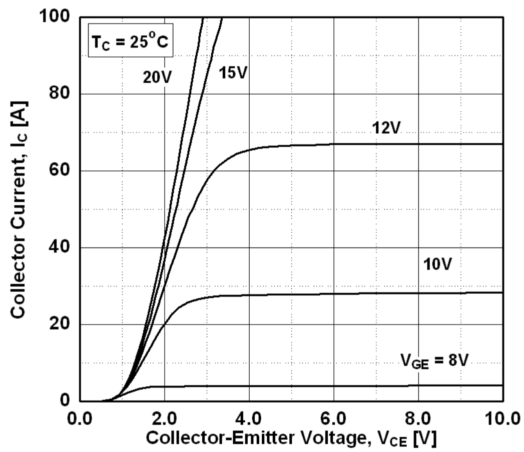


Figure 2. Typical Output Characteristics

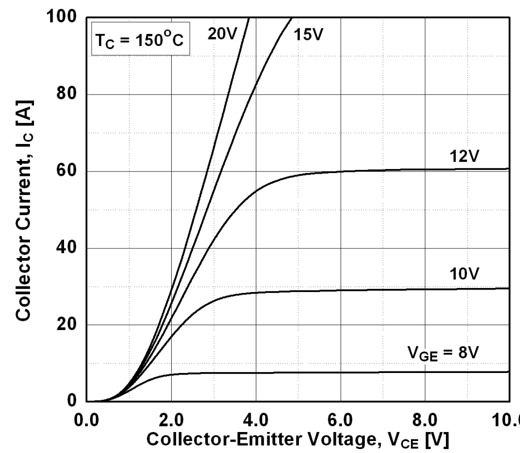


Figure 3. Typical Saturation Voltage Characteristics

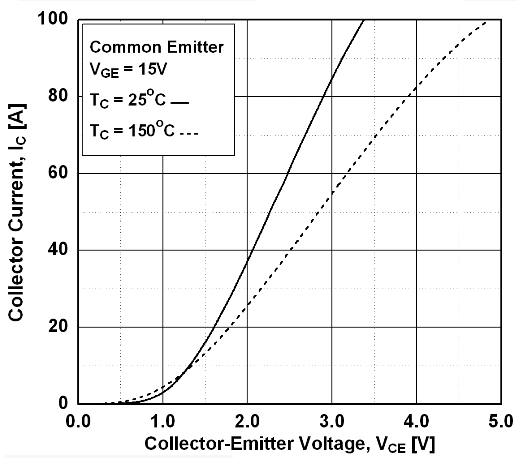


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

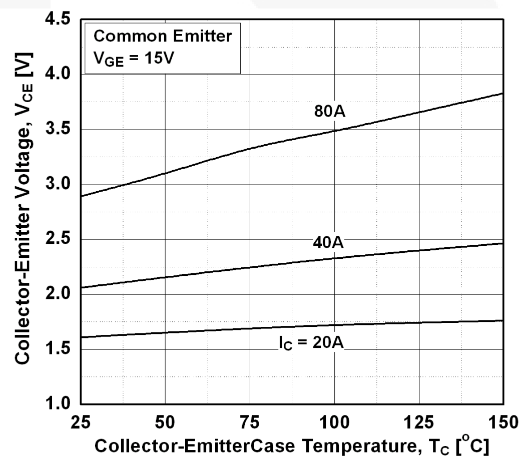


Figure 5. Saturation Voltage vs. V_{GE}

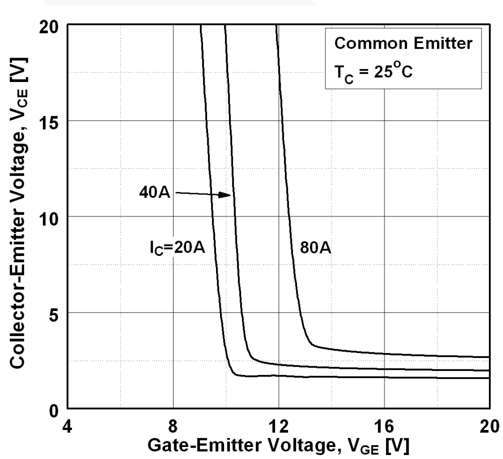
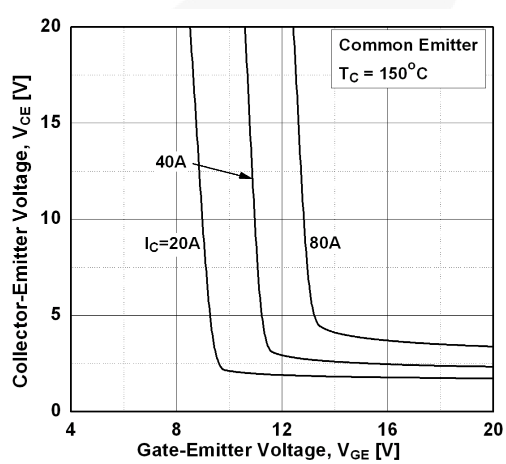


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

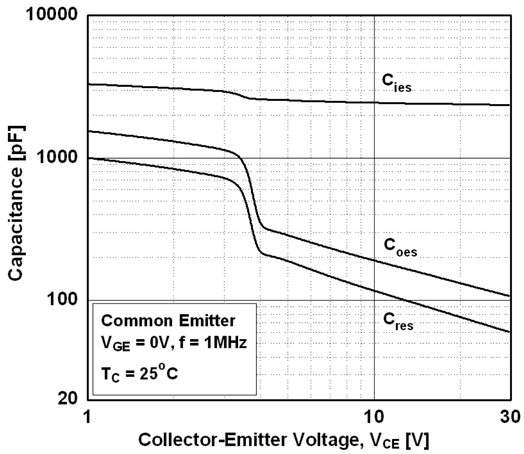


Figure 8. Gate Charge Characteristics

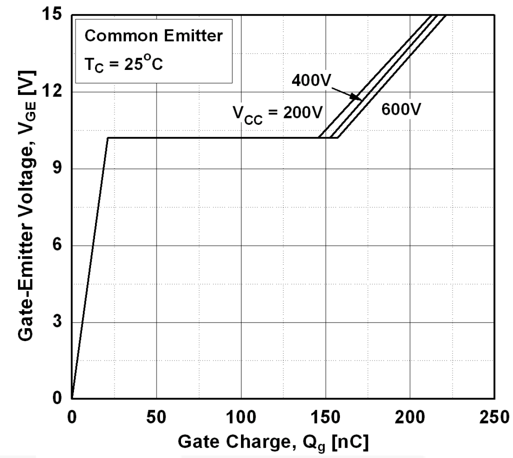


Figure 9. Turn-on Characteristics vs. Gate Resistance

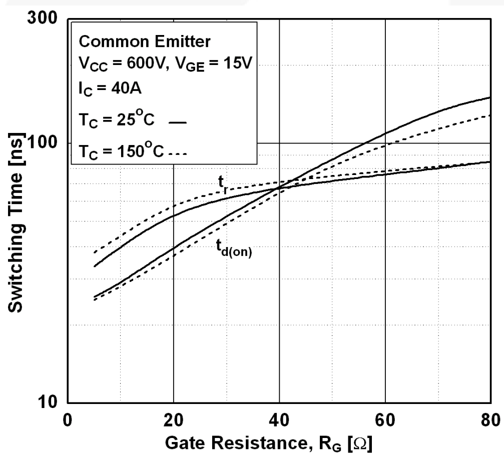


Figure 10. Turn-off Characteristics vs. Gate Resistance

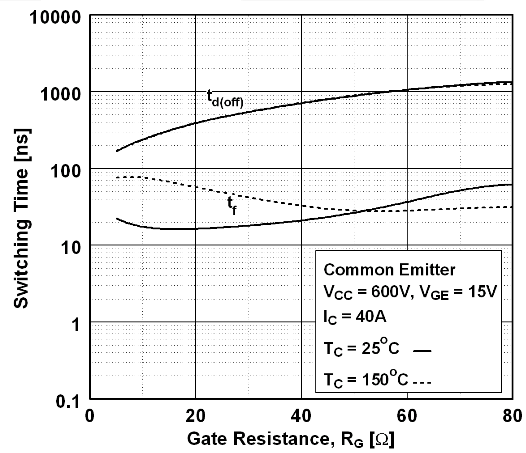


Figure 11. Swithcing Loss vs. Gate Resistance

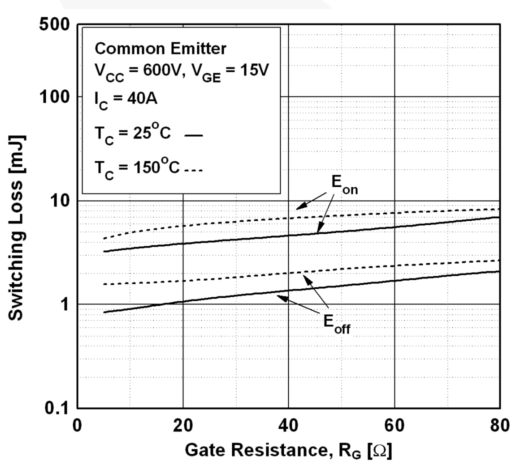
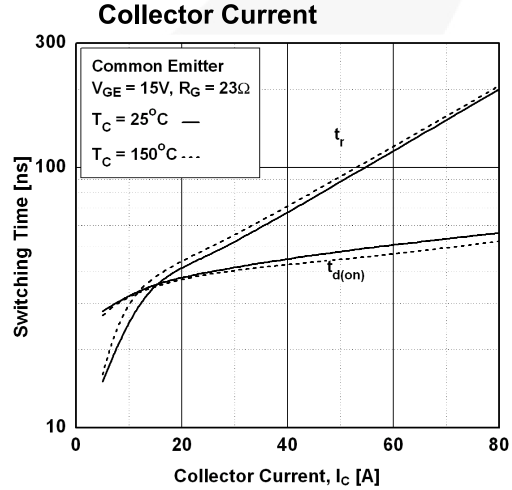


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

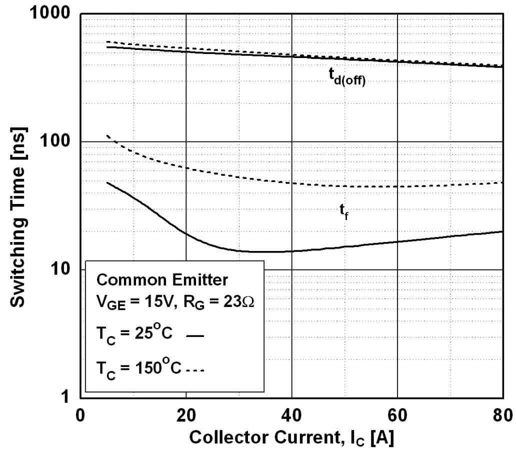


Figure 14. Swithcing Loss vs. Collector Current

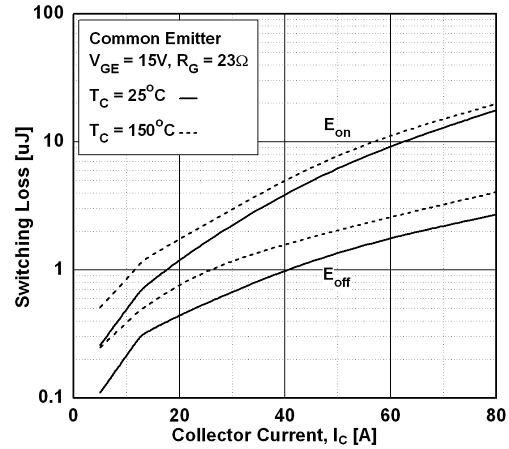


Figure 15. Load Current vs. Frequency

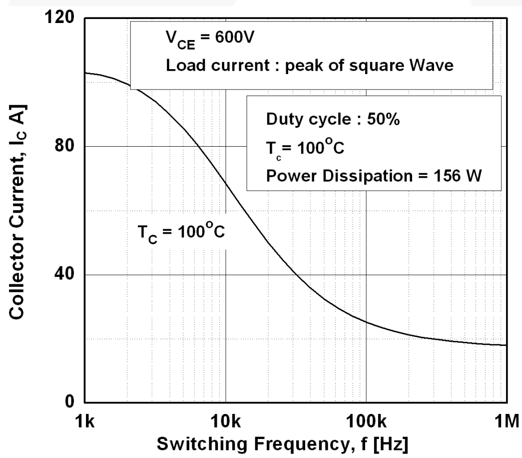


Figure 16. SOA Characteristics

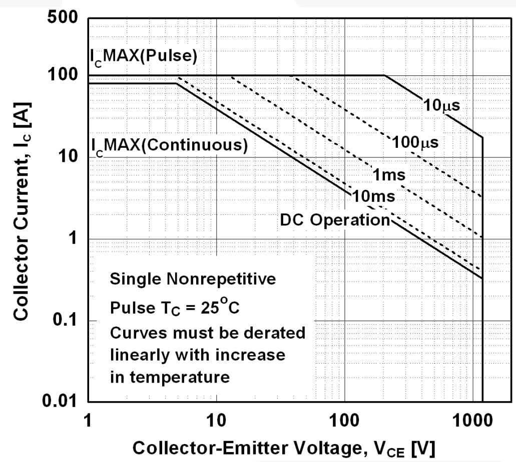


Figure 17. Forward Characteristics

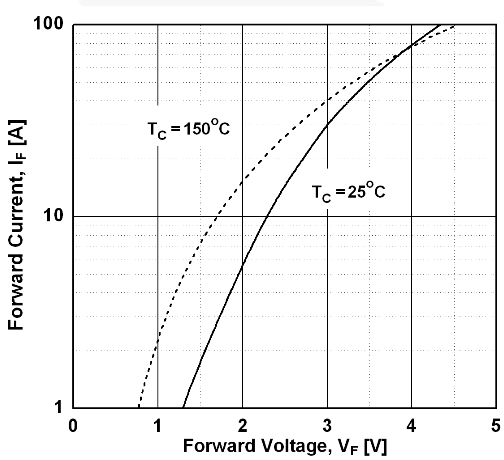
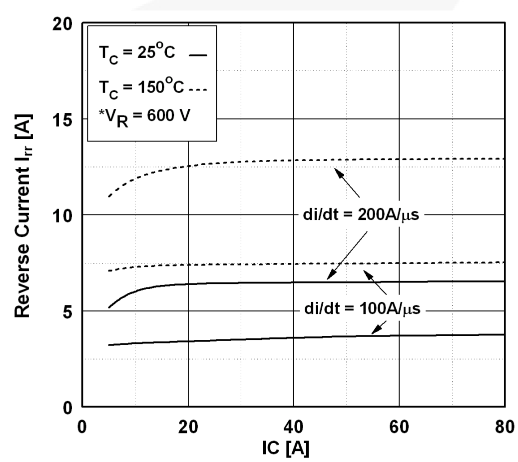


Figure 18. Reverse Recovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

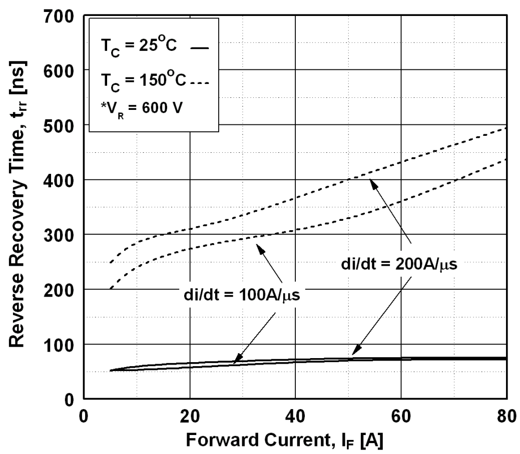


Figure 20. Stored Charge

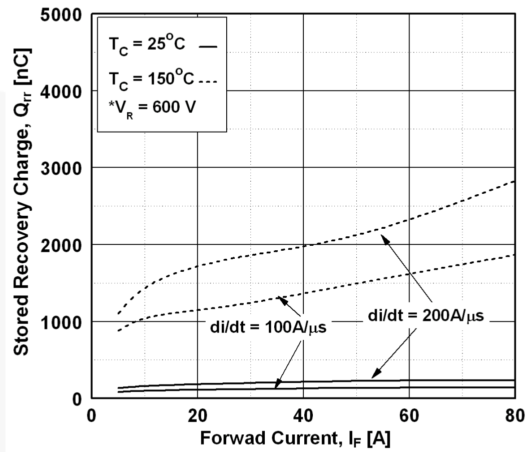


Figure 21. Transient Thermal Impedance of IGBT

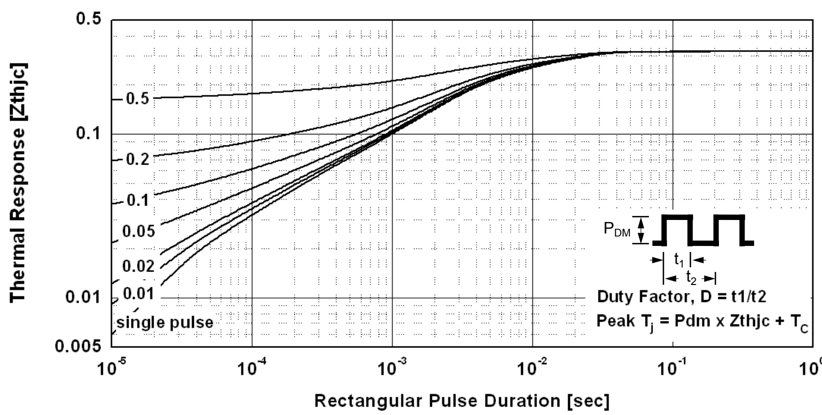
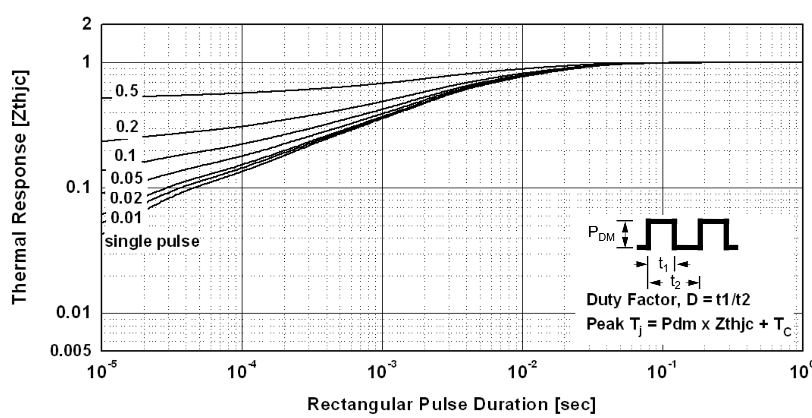


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions

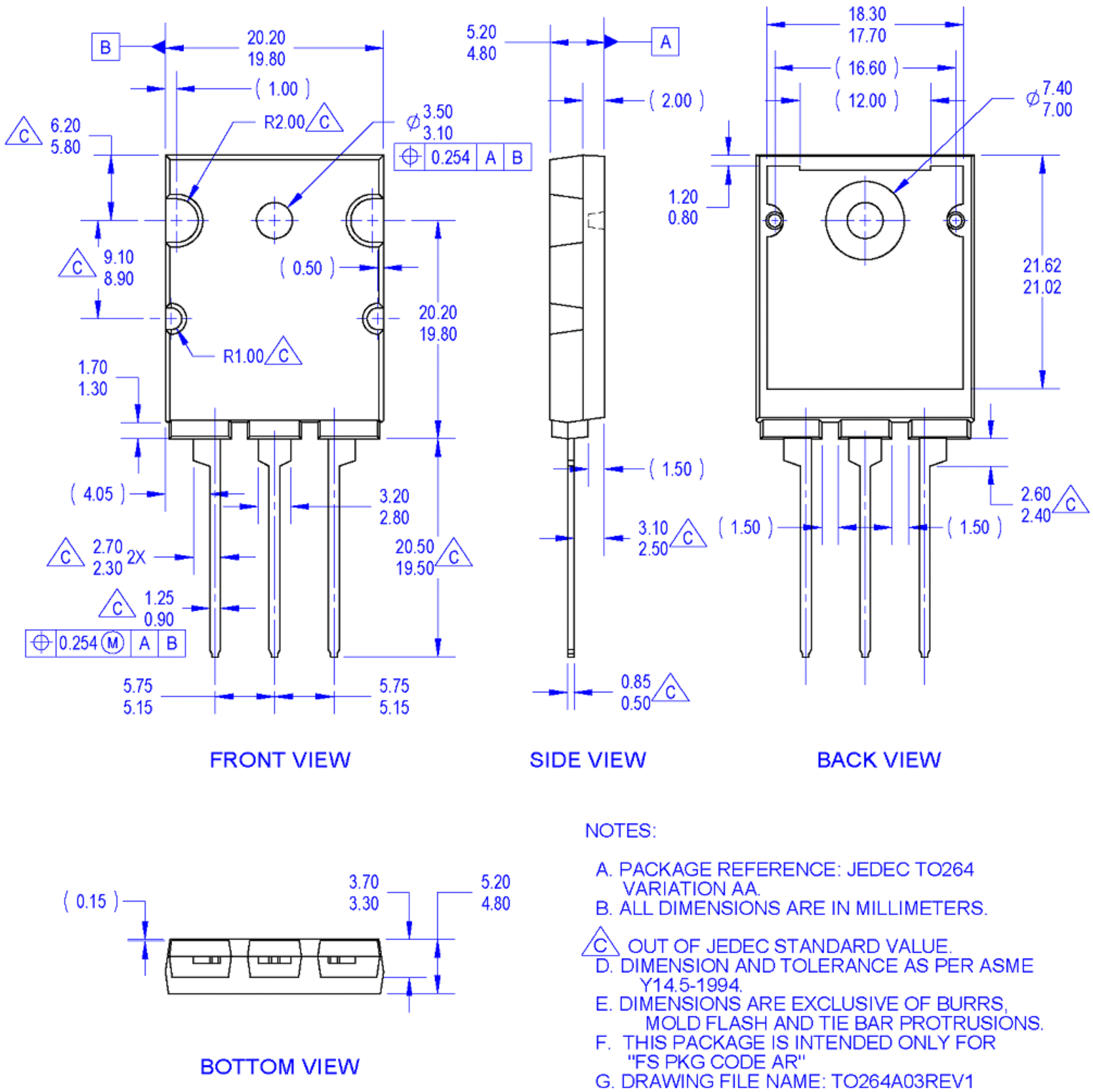


Figure 23. TO264, Molded, 3-Lead, Jedec Variation AA

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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I71

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